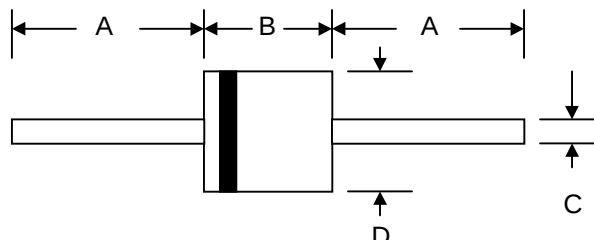


**12SQ030-12SQ100****12A SCHOTTKY BARRIER DIODE****FEATURES**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

**Mechanical Data**

- Case: P-600, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 2.1 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free: For RoHS / Lead Free Version,**

R-6		
Dim	Min	Max
A	25.4	—
B	8.60	9.10
C	1.20	1.30
D	8.60	9.10
All Dimensions in mm		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	12SQ030	12SQ035	12SQ040	12SQ045	12SQ050	12SQ060	12SQ080	12SQ100	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	30	35	40	45	50	60	80	100	V
Maximum RMS Voltage	VRMS	21	24.5	28	31.5	35	42	56	70	V
Maximum DC Blocking Voltage	VDC	30	35	40	45	50	60	80	100	V
Maximum Average Forward Rectified Current@Tc=95 °C	I(AV)	12								A
Peak Forward Surage Current 8.3ms single half sine-wave super imposed on rated load(JEDEC Method)	IFSM	275								A
Peak Forward Voltage at 10A DC(Note1)	VF	0.55				0.7		0.8		V
Maximum DC Reverse Current @Tj=25℃ at Rated DC Bolcking Voltage @Tj=100℃	IR	0.5 50								mA
Tyical Junction Capacitance (Note2)	CJ	450								PF
Tyical Thermal Resistance (Note3)	R J	3.0								℃/w
Operating Temperature Range	TJ	-55 to+200								℃
Storage Temperature Range	TSTG	-55 to+200								℃

NOTES:1.300us Pulse Width, 2%Duty Cycle.

2.Measured at 1.0 MHZ and applied reverse voltage of 4.0VDC.

3.Thermal Resistance Junction to Case.



12SQ030-12SQ100



FIG.1-FORWARD CURRENT DERATING CURVE

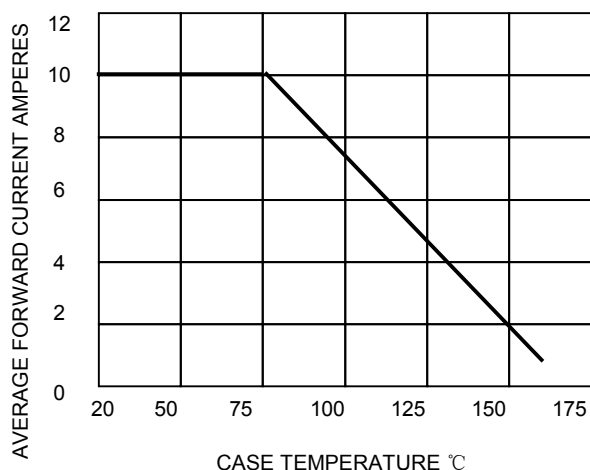


FIG.2-MAXIMUM NON-REPETITIVE SURGE

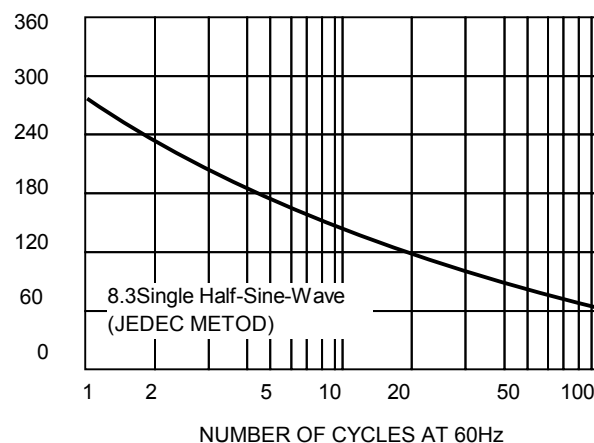


FIG.3-TYPICAL REVERSE CHARACTERISTICS

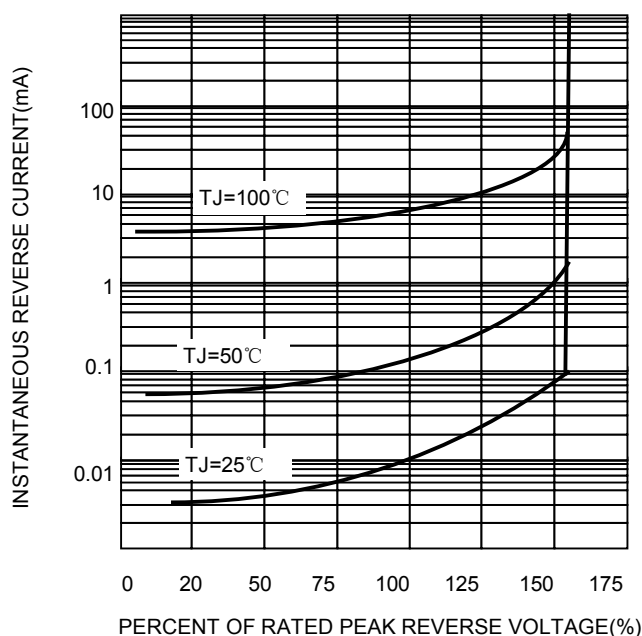


FIG.4-TYPICAL FORWARD CHARACTERISTICS

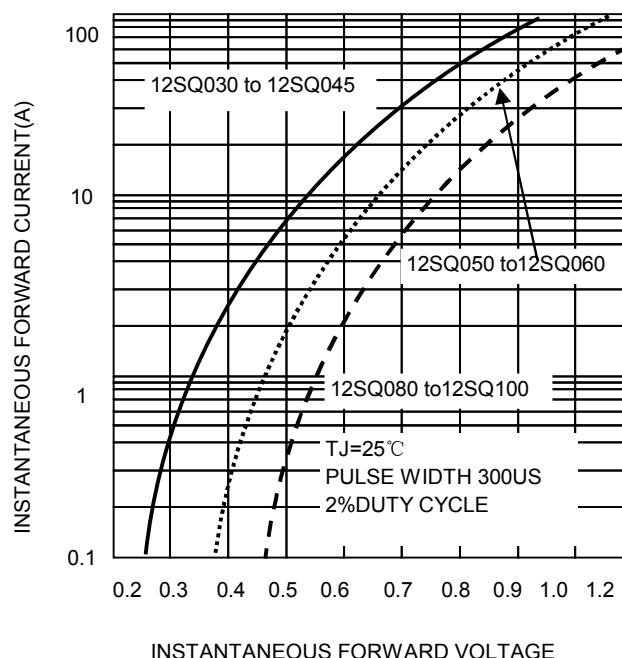


FIG.5-TYPICAL JUNCTION CAPACITANCE

